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Docket No. : SON-1285/DIV PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent No. 7,355,214

Confirmation No. 5551

Inventor: Takashi Noguchi et al.

Patented: April 8, 2008

For: FIELD EFFECT TRANSISTOR AND FABRICATION THEREOF,
SEMICONDUCTOR DEVICE AND FABRICATION THEREOF, LOGIC CIRCUIT
INCLUDING THE SEMICONDUCTOR DEVICE, AND SEMICONDUCTOR
SUBSTRATE

REQUEST FOR CERTIFICATE OF CORRECTION

MS: CERTIFICATE OF CORRECTION

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Certificate
JUN 11 2008
of Correction

Sir:

It is respectfully requested that a Certificate of Correction be issued in connection with the above-identified patent. It appears that the error noted is a mistake of a typographical nature, and was made by the attorneys for the Applicant. The mistake was made in good faith and correction thereof would not constitute new matter or require reexamination. Accordingly, two copies of the special Certificate of Correction are attached hereto. It is believed that the error noted is an error of consequence involving claim language and thus warrants the granting of a Certificate of Correction.

Please charge Deposit Account No. 18-0013 the \$100.00 fee set forth in 37

C.F.R. § 1.20(a). If additional costs are required, please treat this as authorization to charge such further costs.

Respectfully submitted,

Dated: June 9, 2008

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Patent Publication

JUN 12 2008

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,355,214

DATED : April 8, 2008

INVENTOR(S) : Takashi Noguchi et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below: .

Column 18, Line 62:

"Si_{1-x}Ge_x³" should read -- Si_{1-x}Ge_x --.

MAILING ADDRESS OF SENDER:

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PATENT NO. 7,355,214

Our Ref: SON-1285/DIV
FORM PTO 1050 (REV. 3-82)

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UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,355,214

DATED : April 8, 2008

INVENTOR(S) : Takashi Noguchi et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 18, Line 62:

"Si_{1-x}Ge_x3" should read -- Si_{1-x}Ge_x --.

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